L Number	Hits	Search Text	DB	Time stamp
1	2	("5942032").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:02
2	1262	((117/13) or (117/19) or (117/21) or (117/34)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:02
3	17	(((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:04
4	13	(((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:13
5	455	(257/620).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:14
6	362	(438/906).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:14
7	0	(437/83).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:14
8	0	(437/84).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:15
9	413	(117/84).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:15
10	1229	((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.) or ((117/84).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:15
11	4	(((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.) or ((117/84).CCLS.)) and czochralski and (hydrogen or "H.sub.2") near15 (vacuum or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/13 17:16
-	1154	((257/620) or (438/906) or (437/83) or (437/84) or (117/19) or (117/84)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 18:01
-	1	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (hydrogen with dop$3 with silicon with wafer) same concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:09

-	90	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:10
-	18	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and heat adj shield	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:11
-	37	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and nitrogen with dop$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:11
-	43	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (argon with hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:12
-	201	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:12
-	1	single adj silicon adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:14
-	54	silicon adj single adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:14
-	805	(117/13).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	0	(("117/13").CCLS.) and heat adj sjield.ti,ab. and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	5	(("117/13").CCLS.) and heat adj shield.ti,ab. and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 19:17
-	43	trench adj mosfet.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 20:15
-	9	(trench adj mosfet.ti.) and 257/$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/05 20:15
-	4	"6191009"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/29 12:24
-	5	(("6191009") or ("6299982") or ("5942032") or ("6224668") or ("6197109")).PN.	USPAT	2002/01/29 12:25
-	5	(("6191009") or ("6299982") or ("5942032") or ("6244668") or ("6197109")).PN.	USPAT	2002/02/01 11:22

-	1	("6224668").PN.	USPAT	2002/02/01 11:29
-	4	("4210486").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 16:22
-	410	(liquid adj crystal adj display or lcd).ti. and 257/$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 16:23
-	64	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar) (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 17:56
-	64	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar) (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 17:59
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:01
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:02
-	1	method.clm. and silicon.ti,ab. and wafer.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:03
-	1	method.clm. and silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:03
-	1	silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:04
-	1	silicon and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:05
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
-	1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:07

–		22	silicon and (h or hydrogen) and pressure and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:20
–		5	czochralski and pressure near3 mbar and oxygen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:21
–		23	czochralski.ti,ab. and pressure near3 argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
–		5	czochralski.ti,ab. and pressure near3 argon near3 mbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
–		0	czochralski.ti,ab. and pressure near3 argon near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
–		3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
–		3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39
–		3	czochralski.ti,ab. and pressure near3 mbar near3 argon and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39
–		13	czochralski and (noble or inert or argon) near4 mbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 13:51
–		2	("6291874").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 14:11
–		2	("6299892").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 15:37
–		3	(zone-drawing or zone adj drawing) near12 czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 16:07
–		6	(("6291874") or ("4330361")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/20 16:07
–		2	("6291874").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 20:43

–	3	("4330361").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 21:05
–	41	pulling near3 czochralski near12 melting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 21:13
–	0	pulling near12 czochralski near12 melting near12 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 21:13
–	1	pulling near17 czochralski near17 melting near17 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/05 21:13
–	2	("6388286").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/06 12:18
–	2	("6194283").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/06 12:16
–	2	("4890144").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/06 12:20
–	2	("6323090").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/06 12:20
–	0	("hydrogen near2 pressure and czochralski.it,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 18:01
–	4	hydrogen near2 pressure and czochralski.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 18:02
–	5	(single-crystalline or single-crystal).ti,ab,clm. and stacking adj fault.ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:33
–	185	(single-crystalline or single-crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:34
–	0	(single-crystalline or single-crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (mbar or Hg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:35
–	0	(single-crystalline or single-crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (mbar or mtorr or Hg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:35

-	22	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (mbar or mtorr or Hg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:36
-	35	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:37
-	0	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:40
-	1	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or impurity or doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:41
-	1	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or impurity or doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:42
-	2	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near15 (atm or pascal or mbar or mtorr or Hg) and ("n.sub.2" or nitrogen) near15 (doping or impurity or doped or impurities)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:43
-	996	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:44
-	551	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:44
-	240	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:45
-	5	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. near20 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:48

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–	0	czochralski.ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. near20 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:49
–	0	(czochralski or cz-silicon).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. near20 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:53
–	68	(czochralski or cz-silicon and single-crystalline or single-crystal or single adj crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) near12 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:54
–	1207	(czochralski or cz-silicon and single-crystalline or single-crystal or single adj crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) near12 (mbar or pascal or mtorr) stacking adj fault and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:55
–	6	(czochralski or cz-silicon and single-crystalline or single-crystal or single adj crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) near12 (mbar or pascal or mtorr) and stacking adj fault and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:55
–	2	("5993557").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:04
–	23	(cz-silicon or czochralski).ti,ab,clm. and stacking adj fault and (hydrogen or "H.sub.2") and (pressure or vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:12
–	6	(cz-silicon or czochralski).ti,ab,clm. and stacking adj fault and (hydrogen or "H.sub.2") and (pressure or vacuum) and "shin-etsu"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:07
–	11	(cz-silicon or czochralski).ti,ab,clm. and stacking adj fault and (hydrogen or "H.sub.2") and (pressure or vacuum) and (mbar or bar or atm or pascal or torr or mtorr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:13
–	4	(cz-silicon or czochralski).ti,ab,clm. and stacking adj fault and (hydrogen or "H.sub.2") and (pressure or vacuum) near15 (mbar or bar or atm or pascal or torr or mtorr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:17
–	0	(cz-silicon or czochralski).ti,ab,clm. and stacking adj fault and (hydrogen or "H.sub.2") near25 (pressure or vacuum) near25 (mbar or bar or atm or pascal or torr or mtorr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:18
–	7	(cz-silicon or czochralski).ti,ab,clm. and (hydrogen or "H.sub.2") near25 (pressure or vacuum) near25 (mbar or bar or atm or pascal or torr or mtorr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:28
–	0	stacking adj fault near15 hydrogen near15 (mbar or mtorr or pascal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:29

-	4	stacking adj fault and hydrogen near15 (mbar or mtorr or pascal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:30
-	80	"shin-etsu" and hydrogen and (czochralski or cz-silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:31
-	5	"shin-etsu" and hydrogen near15 pressure and (czochralski or cz-silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:32
-	5	"shin-etsu" and hydrogen near15 pressure and (czochralski or cz-silicon or cz adj method)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 14:32
-	3	("4330361").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 18:15

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